

# UC Irvine

## UC Irvine Previously Published Works

### Title

Recovery of Voltage-Gated Nav1.4 Channels from Slow Inactivation Reflects Memory of Prior Stimulation in Multiple Molecular Processes

### Permalink

<https://escholarship.org/uc/item/68z6j015>

### Journal

Biophysical Journal, 98(3)

### ISSN

0006-3495

### Authors

Silva, Jonathan R  
Goldstein, Steve AN

### Publication Date

2010

### DOI

10.1016/j.bpj.2009.12.4197

### Copyright Information

This work is made available under the terms of a Creative Commons Attribution License, available at <https://creativecommons.org/licenses/by/4.0/>

Peer reviewed

**582-Pos****Recovery of Voltage-Gated Na<sub>v</sub>1.4 Channels from Slow Inactivation Reflects Memory of Prior Stimulation in Multiple Molecular Processes****Jonathan R. Silva**, Steve A.N. Goldstein.

Institute for Molecular Pediatric Science, University of Chicago, Chicago, IL, USA.

Slow inactivation (SI) regulates availability of voltage-gated Na<sup>+</sup> (Na<sub>v</sub>) channels in neurons, cardiac myocytes and skeletal muscle cells thereby determining excitability. In native cells, inactive Na<sub>v</sub> channels accumulate when the time between action potentials is inadequate to allow recovery from SI. SI can be simulated with cloned channels by repetitive application of seconds-long depolarizing pulses to cells expressing the channels. Others have shown that, in contrast to voltage-gated K<sup>+</sup> channels, the rate of recovery from SI for Na<sub>v</sub>1.2 channels (a neuronal isoform) depends on the duration of the previous depolarizing pulse - the channels show memory (Toib et al. 1998. J. Neurosci. 18:1893-903). To investigate this phenomenon in Na<sub>v</sub>1.4 channels (a muscle isoform), we measure ionic and gating currents in cut-open oocyte mode and employ voltage clamp fluorimetry to correlate motion of each of the four S4 voltage sensing domains with currents. Like Na<sub>v</sub>1.2, Na<sub>v</sub>1.4 recovery from SI is found to depend on prepulse duration. A model for memory of prepulse duration is proposed based on the kinetics of processes associated with specific S4 domains and others independent of gating charge movement.